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DATE MAILED: 06/02/2003

APPLICATION NO. FILING DATE FIRST NAMED INVENTOR ATTORNEY DOCKET NO. CONFIRMATION NO. 09/888,365 06/22/2001 Stephen DeOrnellas TEGL-01092US1 8894 23910 06/02/2003 FLIESLER DUBB MEYER & LOVEJOY, LLP **EXAMINER** FOUR EMBARCADERO CENTER ALEJANDRO MULERO, LUZ L **SUITE 400** SAN FRANCISCO, CA 94111 ART UNIT PAPER NUMBER 1763

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Applica	ition No.	Applicant(s)	J	
,		09/888	,365	DEORNELLAS	DEORNELLAS ET AL.	
Office Action Summary		Examir	er	Art Unit	<u> </u>	
		Luz L. A	Nejandro	1763		
The Period for Rep	MAILING DATE of this commun	ication appears on	he cover s	heet with the correspondence	address	
A SHORTEL THE MAILIN - Extensions of after SIX (6) M - If the period fo - If NO period fo - Failure to reply - Any reply rece	NED STATUTORY PERIOD FO NG DATE OF THIS COMMUNI time may be available under the provisions MONTHS from the mailing date of this common or reply specified above is less than thirty (30 or reply is specified above, the maximum starty by within the set or extended period for reply- dived by the Office later than three months at term adjustment. See 37 CFR 1.704(b).	CATION. of 37 CFR 1.136(a). In no unication. o) days, a reply within the s tutory period will apply and will. by statute, cause the a	event, howeve tatutory minim will expire SIX	r, may a reply be timely filed um of thirty (30) days will be considered ti (6) MONTHS from the mailing date of th	mely. s communication.	
1)⊠ Resp	onsive to communication(s) file	ed on <u>21 March 20</u>	<u>93</u> .			
2a)☐ This	action is FINAL.	2b)⊠ This action	is non-fina	il.		
3) Since close Disposition of	e this application is in condition ed in accordance with the pract Claims	for allowance exc ice under <i>Ex parte</i>	ept for form Q <i>uayle</i> , 19	nal matters, prosecution as to 935 C.D. 11, 453 O.G. 213.	the merits is	
4) Claim(s) 12-16,19,30,31 and 56-63 is/are pending in the application.						
4a) Of	the above claim(s) is/ar	e withdrawn from o	onsiderati	on.		
5)☐ Claim((s) is/are allowed.					
6)⊠ Claim(s) <u>12-16,19,30,31 and 56-63</u> is/are rejected.						
7)☐ Claim(7) Claim(s) is/are objected to.					
8) Claim(Application Par	(s) are subject to restrict	ion and/or election	requireme	ent.		
9)□ The sp	ecification is objected to by the	Examiner.				
10)□ The dra	awing(s) filed on is/are:	a) accepted or b)	objected	to by the Examiner.		
	cant may not request that any obje				1).	
	posed drawing correction filed					
	roved, corrected drawings are req					
12)☐ The oat	th or declaration is objected to	by the Examiner.				
Priority under 3	5 U.S.C. §§ 119 and 120					
13)☐ Acknov	wledgment is made of a claim t	or foreign priority u	nder 35 U	.S.C. § 119(a)-(d) or (f).		
	b)☐ Some * c)☐ None of:			,		
1 (Certified copies of the priority d	ocuments have be	en receive	d.		
2. 🗌 (2. Certified copies of the priority documents have been received in Application No					
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
	edgment is made of a claim for				al application)	
_ a) 🔲 The	e translation of the foreign lang ledgment is made of a claim fo	uage provisional a	oplication	has been received.	ы арріісацііі).	
Attachment(s)		priority (
Notice of Drafts Information Dis	rences Cited (PTO-892) sperson's Patent Drawing Review (PTo sclosure Statement(s) (PTO-1449) Pap	O-948) er No(s)	4)	erview Summary (PTO-413) Paper N tice of Informal Patent Application (P er:	o(s) TO-152)	
S. Patent and Trademark Off TO-326 (Rev. 04-01)	ice	Office Action Summi		Part of Paper No	42	

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 3-12-03 has been entered.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 12-13, 15, and 30 are rejected under 35 U.S.C. 102(b) as being anticipated by Imai et al., WO 97/27622.

Imai et al. shows the invention as claimed including a method of operating an etch reactor which comprises a reactor chamber 7, an upper electrode 5, a heater 11 that heats said upper electrode, and gas inlets and outlets comprising: introducing process gas into said chamber 7, and heating the upper electrode with said heater 11 to a temperature such that any material resulting from the reaction deposited on the

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surface of the upper electrode forms a stable film comprising halogen elements (see fig. 1 and abstract).

With respect to claim 30, note that in Imai et al. a silicon oxide film is etched which is a non-volatile material.

Claims 12-13, 15, 30, and 56-61 are rejected under 35 U.S.C. 102(b) as being anticipated by Collins et al., U.S. Patent 5,556,501.

Collins et al. shows the invention as claimed including a method of operating an etch reactor which comprises a reactor chamber 16B, an upper electrode 17S with power applied thereto from a RF source 40, a heater that heats said upper electrode (see col. 7-lines 45-50), and gas inlets and outlets comprising: introducing process gas into said chamber 16B, and heating the upper electrode with said heater to a temperature such that any material resulting from the reaction deposited on the surface of the upper electrode forms a stable film comprising halogen elements (see fig. 1 and its description).

With respect to claim 30, note that a variety of materials including non-volatile materials can be etched in Collins et al. (see col. 6-lines 18-30).

Regarding claim 56, note that in an alternative embodiment a side electrode is formed from the walls which are heated (see col. 21-line 43 to col. 22-line 43).

With respect to claims 60-61, note that inherently any gas collected on the upper surface will desorb or boil off from the surface as a result of heating of these surfaces.

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Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

Claim 14 is rejected under 35 U.S.C. 103(a) as being unpatentable over Imai et al., WO 97/27622.

Imai et al. is applied as above but fails to expressly disclose heating the upper electrode to a temperature of about 300 Celsius to about 500 Celsius. However, a prima facie case of obviousness still exists because generally, differences in concentration or temperature will not support the patentability of subject matter encompassed by the prior art unless there is evidence indicating such concentration or temperature is critical. "[W]here the general conditions of a claim are disclosed in the

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prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation." In re Aller, 220 F.2d 454, 456, 105 USPQ 233, 235 (CCPA 1955).

Claim 14 is rejected under 35 U.S.C. 103(a) as being unpatentable over Collins et al., U.S. Patent 5,556,501.

Collins et al. is applied as above but fails to expressly disclose heating the upper electrode to a temperature of about 300 Celsius to about 500 Celsius. However, a prima facie case of obviousness still exists because generally, differences in concentration or temperature will not support the patentability of subject matter encompassed by the prior art unless there is evidence indicating such concentration or temperature is critical. "[W]here the general conditions of a claim are disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation." In re Aller, 220 F.2d 454, 456, 105 USPQ 233, 235 (CCPA 1955).

Claims 16, 19, and 31 are rejected under 35 U.S.C. 103(a) as being unpatentable over Collins et al., U.S. Patent 5,556,501 in view of DeOrnellas et al., WO 99/25568.

Collins et al. is applied as above but fails to expressly disclose a platinum etch method or where oxygen and chlorine are present in the reactor and heating the upper electrode causes deposits of oxygen and chlorine to de-absorb from the upper electrode in order to leave mostly platinum deposited on the surface, or etching one of the materials exemplified in claim 31. However, it should be noted that Collins et al.

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discloses that the apparatus of fig. 1 can be used to etch a variety of materials including etching metals (see col. 6-line 28). DeOrnellas et al. discloses a similar three electrode configuration as in Collins et al. (see fig. 7) where platinum or other materials such as those listed in claim 31 are etched in a chlorine gas and oxygen is inherently present in the chamber (see page 8, line 25 to page 9, line 17). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the process of Collins et al. so as to performing the platinum etching process of DeOrnellas et al. because this would be a suitable method, for example, to reduce the platinum deposits that can form on the wafer.

Claims 16, 19, and 31 are rejected under 35 U.S.C. 103(a) as being unpatentable over Imai et al., WO 97/27622 in view of DeOrnellas et al., WO 99/25568.

Imai et al. is applied as above but fails to expressly disclose a platinum etch method or where oxygen and chlorine are present in the reactor and heating the upper electrode causes deposits of oxygen and chlorine to de-absorb from the upper electrode in order to leave mostly platinum deposited on the surface, or etching one of the materials exemplified in claim 31. DeOrnellas et al. discloses a where platinum or other materials such as those listed in claim 31 are etched in a chlorine gas and oxygen is inherently present in the chamber (see page 8, line 25 to page 9, line 17). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the process of Imai et al. so as to perform the

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platinum etching process of DeOrnellas et al. because this would be a suitable method, for example, to reduce the platinum deposits that can form on the wafer.

Claims 16, 19, and 31 are rejected under 35 U.S.C. 103(a) as being unpatentable over Collins et al., U.S. Patent 5,556,501 in view of Keizo, JP 07-130712A.

Collins et al. is applied as above but fails to expressly disclose a platinum etch method or where oxygen and chlorine are present in the reactor and heating the upper electrode causes deposits of oxygen and chlorine to de-absorb from the upper electrode in order to leave mostly platinum deposited on the surface. However, it should be noted that Collins et al. discloses that the apparatus of fig. 1 can be used to etch a variety of materials including etching metals (see col. 6-line 28). Keizo discloses performing plasma etching of platinum using a chloride containing gas (see abstract). Furthermore, note that inherently oxygen will be present in the chamber. In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the process of Collins et al. so as to performing the platinum etching process of Keizo et al. because this would be a suitable method, for example, to reduce the platinum deposits that can form on the wafer.

Claims 16, 19, and 31 are rejected under 35 U.S.C. 103(a) as being unpatentable over Imai et al., WO 97/27622 in view of Keizo, JP 07-130712A.

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Imai et al. is applied as above but fails to expressly disclose a platinum etch method or where oxygen and chlorine are present in the reactor and heating the upper electrode causes deposits of oxygen and chlorine to de-absorb from the upper electrode in order to leave mostly platinum deposited on the surface. Keizo discloses performing plasma etching of platinum using a chloride containing gas (see abstract). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the process of Imai et al. so as to perform the platinum etching process of Keizo because this would be a suitable method, for example, to reduce the platinum deposits that can form on the wafer.

Claims 56-61 are rejected under 35 U.S.C. 103(a) as being unpatentable over Imai et al., WO 97/27622 in view of Collins et al., U.S. Patent 5,556,501.

Imai et al. is applied as above but fails to expressly disclose providing power to the upper electrode and a three electrode structure with a side electrode which is heated. Collins et al. discloses an upper electrode 17S with power applied thereto from a RF source 40 and an alternative embodiment in which a side electrode is formed from the walls which are heated (see col. 21-line 43 to col. 22-line 43). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the process of Imai et al. so as to provide power to the upper electrode and use a three electrode structure as disclosed by Collins et al. because providing power to the upper electrode allows for the flexibility of both inductive

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and capacitive coupling during the etching process and the three electrode process allows for additional process control and enhancement (see col. 21-lines 44-46).

With respect to claims 60-61, note that inherently any gas collected on the upper surface will desorb or boil off from the surface as a result of heating of these surfaces.

Claims 62-63 are rejected under 35 U.S.C. 103(a) as being unpatentable over Imai et al., WO 97/27622 in view of Yamazaki et al., U.S. Patent 6,001,432.

Imai et al. is applied as above but fails to expressly disclose the upper electrode having an electrode shield formed thereon. Yamazaki et al. discloses a plasma apparatus where an electrode shield 4 is formed on an upper electrode 3 (see fig. 1, for example, and its description). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the process of Imai et al. so as to form an electrode shield on the upper electrode because this will protect the upper electrode itself from exposure to the plasma.

Claims 62-63 are rejected under 35 U.S.C. 103(a) as being unpatentable over Collins et al., U.S. Patent 5,556,501 in view of Yamazaki et al., U.S. Patent 6,001,432.

Collins et al. is applied as above but fails to expressly disclose the upper electrode having an electrode shield formed thereon. Yamazaki et al. discloses a plasma apparatus where an electrode shield 4 is formed on an upper electrode 3 (see fig. 1, for example, and its description). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify

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the process of Collins et al. so as to form an electrode shield on the upper electrode because this will protect the upper electrode itself from exposure to the plasma.

Response to Arguments

Applicant's arguments with respect to claims 12-16, 19, 30-31, and 56-63 have been considered but are most in view of the new ground(s) of rejection.

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Imai et al., U.S. Patent 6,214,740, is the US equivalent of WO 97/27622.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Luz L. Alejandro whose telephone number is 703-305-4545. The examiner can normally be reached on Monday to Thursday from 7:30 to 6:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Gregory L. Mills can be reached on 703-308-1633. The fax phone numbers for the organization where this application or proceeding is assigned are 703-872-9310 for regular communications and 703-872-9311 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0661.

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Luz L. Alejandro Primary Examiner Art Unit 1763

May 30, 2003